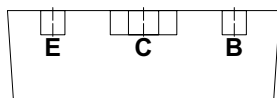
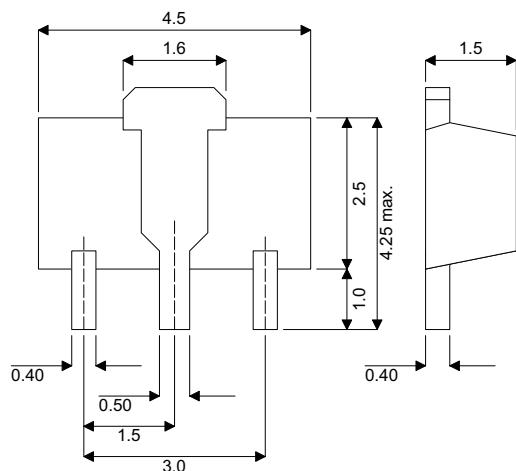


MECHANICAL DATA

Dimensions in mm



SOT89

NPN EPITAXIAL PLANAR SILICON TRANSISTOR

Ideal for high current driver applications requiring low loss devices

FEATURES

- LOW $V_{CE(SAT)}$
- HIGH CURRENT
- HIGH ENERGY RATING

APPLICATIONS

- ANY HIGH CURRENT DRIVER APPLICATIONS REQUIRING EFFICIENT LOW LOSS DEVICES

ABSOLUTE MAXIMUM RATINGS ($T_{case} = 25^{\circ}C$ unless otherwise stated)

V_{CBO}	Collector – Base voltage	30V
V_{CEO}	Collector – Emitter voltage ($I_B = 0$)	10V
V_{EBO}	Emitter – Base voltage	6V
I_C	Collector current	3A
I_{CP}	Collector Current (Pulse)	5A
P_C	Collector Dissipation	500mW
	(Mounted on Ceramic Board (250mm ² x 0.8mm))	1.3W
T_j	Junction Temperature	150°C
T_{stg}	Storage Temperature	-55 to 150°C

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise stated)

Parameter	Test Conditions	Min.	Typ.	Max.	Unit.
V _{(BR)CEO} Collector – Emitter Base Breakdown Voltage	I _C = 1mA R _{BE} = 0	10			V
V _{(BR)CBO} Collector – Base Breakdown Voltage	I _C = 10μA I _E = 0	30			V
V _{(BR)EBO} Emitter Base Breakdown Voltage	I _C = 0 I _E = 10μA	6			V
I _{CBO} Collector Cut-Off Current	V _{CB} = 20V I _E = 0			100	nA
I _{EBO} Emitter Cut-Off Current	V _{BE} = 4V I _C = 0			100	nA
h _{FE} DC Current Gain	V _{CE} = 2V I _C = 3A	140	210		—
f _T Transition frequency	V _{CE} = 10V I _C = 50mA		200		MHz
C _{ob} Output Capacitance	V _{CB} = 10V f = 1MHz	30			pF

